TrenchMOS™ transistor Standard level FET

PHB69N03T

GENERAL DESCRIPTION

N-channel enhancement mode standard level field-effect power transistor in a plastic envelope suitable for surface mounting using '**trench**' technology. The device features very low on-state resistance and has integral zener diodes giving ESD protection up to 2kV. It is intended for use in DC-DC converters and general purpose switching applications.

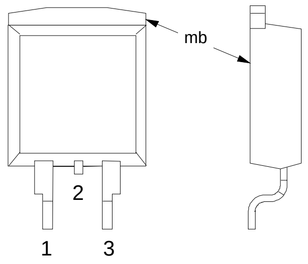
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DS}	Drain-source voltage	30	V
I_D	Drain current (DC)	69	A
P_{tot}	Total power dissipation	125	W
T_j	Junction temperature	175	˚C
$R_{DS(ON)}$	Drain-source on-state resistance V_{GS} = 10 V	14	mΩ

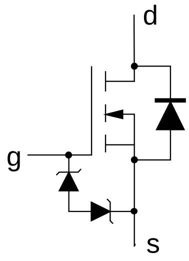
PINNING - SOT404

PIN	DESCRIPTION
1	gate
2	drain
3	source
mb	drain

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Drain-source voltage	-	-	30	V
V_{DGR}	Drain-gate voltage	R_{GS} = 20 kΩ	-	30	V
$\pm V_{GS}$	Gate-source voltage	-	-	20	V
I_D	Drain current (DC)	T_{mb} = 25 ˚C	-	69	A
I_D	Drain current (DC)	T_{mb} = 100 ˚C	-	48	A
I_{DM}	Drain current (pulse peak value)	T_{mb} = 25 ˚C	-	240	A
P_{tot}	Total power dissipation	T_{mb} = 25 ˚C	-	125	W
T_{stg}, T_j	Storage & operating temperature	-	- 55	175	˚C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base	-	-	1.2	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	minimum footprint, FR4 board	50	-	K/W

ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_C	Electrostatic discharge capacitor voltage, all pins	Human body model (100 pF, 1.5 kΩ)	-	2	kV

STATIC CHARACTERISTICS

T_j= 25˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.25 mA;	30	-	-	V
		T_j = -55˚C	27	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	V_{DS} = V_{GS}; I_D = 1 mA	2.0	3.0	4.0	V
		T_j = 175˚C	1.0	-	-	V
		T_j = -55˚C	-	-	4.4	V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 30 V; V_{GS} = 0 V;	-	0.05	10	µA
		T_j = 175˚C	-	-	500	µA
I_{GSS}	Gate source leakage current	V_{GS} = ±10 V; V_{DS} = 0 V	-	0.02	1	µA
		T_j = 175˚C	-	-	20	µA
$\pm V_{(BR)GSS}$	Gate-source breakdown voltage	I_G = ±1 mA;	16	-	-	V
$R_{DS(ON)}$	Drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A	-	12	14	mΩ
		T_j = 175˚C	-	-	26	mΩ

DYNAMIC CHARACTERISTICS

T_{mb} = 25˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	V_{DS} = 25 V; I_D = 25 A	9	18	-	S
$Q_{g(tot)}$	Total gate charge	I_D = 69 A; V_{DD} = 24 V; V_{GS} = 10 V	-	38	-	nC
Q_{gs}	Gate-source charge		-	7	-	nC
Q_{gd}	Gate-drain (Miller) charge		-	14	-	nC
C_{iss}	Input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz	-	1500	2000	pF
C_{oss}	Output capacitance		-	480	550	pF
C_{rss}	Feedback capacitance		-	220	300	pF
$t_{d\ on}$	Turn-on delay time	V_{DD} = 25 V; I_D = 25 A;	-	22	35	ns
t_r	Turn-on rise time	V_{GS} = 10 V; R_G = 5 Ω	-	30	60	ns
$t_{d\ off}$	Turn-off delay time	Resistive load	-	40	50	ns
t_f	Turn-off fall time		-	25	38	ns
L_d	Internal drain inductance	Measured from tab to centre of die	-	3.5	-	nH
L_d	Internal drain inductance	Measured from drain lead solder point to centre of die	-	4.5	-	nH
L_s	Internal source inductance	Measured from source lead solder point to source bond pad	-	7.5	-	nH

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

T_j = 25˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current		-	-	69	A
I_{DRM}	Pulsed reverse drain current		-	-	240	A
V_{SD}	Diode forward voltage	I_F = 25 A; V_{GS} = 0 V	-	0.95	1.2	V
		I_F = 69 A; V_{GS} = 0 V	-	1.0	-	V
t_{rr}	Reverse recovery time	I_F = 69 A; -dI_F/dt = 100 A/µs;	-	60	-	ns
Q_{rr}	Reverse recovery charge	V_{GS} = -10 V; V_R = 25 V	-	0.1	-	µC

AVALANCHE LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
W_{DSS}	Drain-source non-repetitive unclamped inductive turn-off energy	$I_D = 36$ A; $V_{DD} \leq 15$ V; $V_{GS} = 10$ V; $R_{GS} = 50\ \Omega$; $T_{mb} = 25$ ˚C	-	-	125	mJ

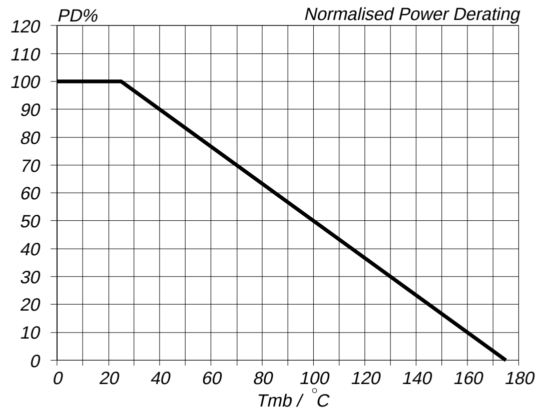


Fig.1. Normalised power dissipation.
PD% = 100·P_D/$P_{D\ 25\ °C}$ = f(T_{mb})

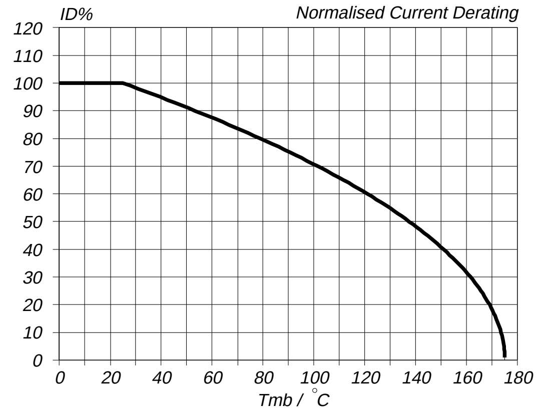


Fig.2. Normalised continuous drain current.
ID% = 100·I_D/$I_{D\ 25\ °C}$ = f(T_{mb}); conditions: V_{GS} ≥ 10 V

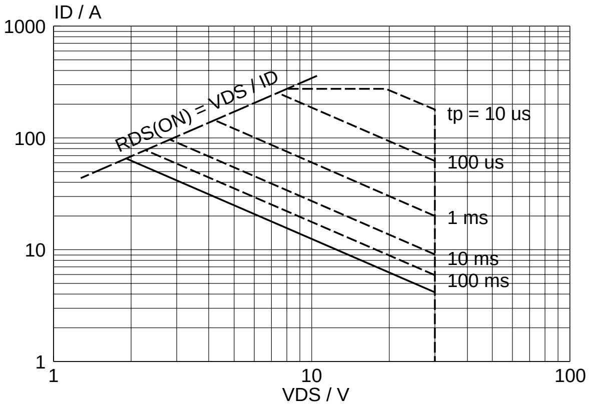


Fig.3. Safe operating area. T_{mb} = 25 ˚C
I_D & I_{DM} = f(V_{DS}); I_{DM} single pulse; parameter t_p

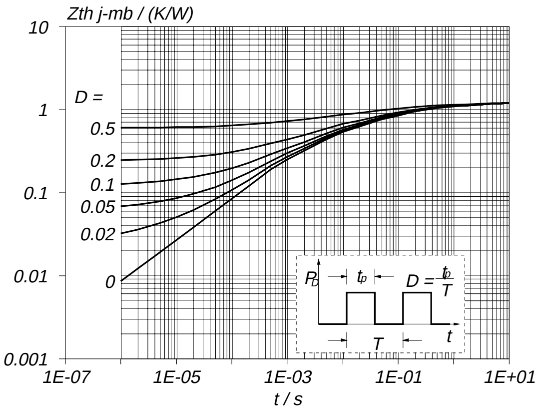


Fig.4. Transient thermal impedance.
$Z_{th\ j\text{-}mb}$ = f(t); parameter D = t_p/T

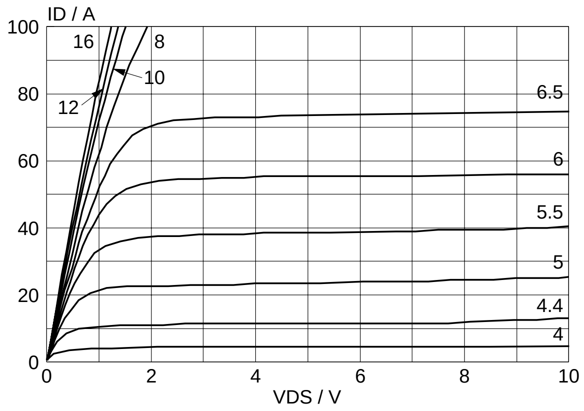


Fig.5. Typical output characteristics, T_j = 25 ˚C.
I_D = f(V_{DS}); parameter V_{GS}

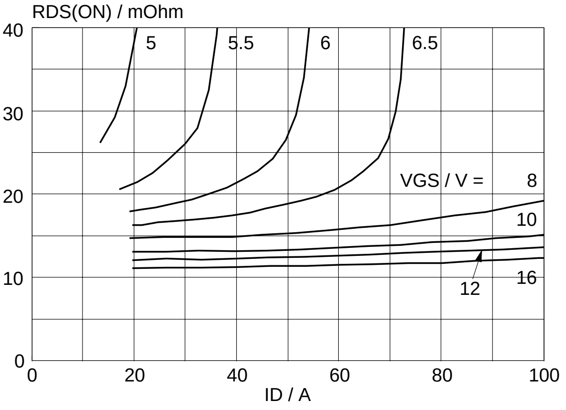


Fig.6. Typical on-state resistance, T_j = 25 ˚C.
$R_{DS(ON)}$ = f(I_D); parameter V_{GS}

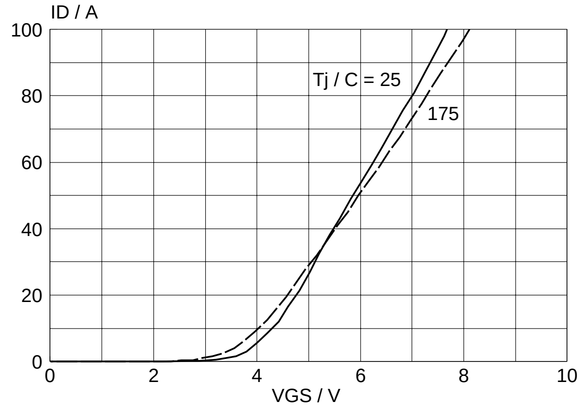


Fig.7. Typical transfer characteristics.
$I_D = f(V_{GS})$; conditions: $V_{DS} = 25$ V; parameter T_j

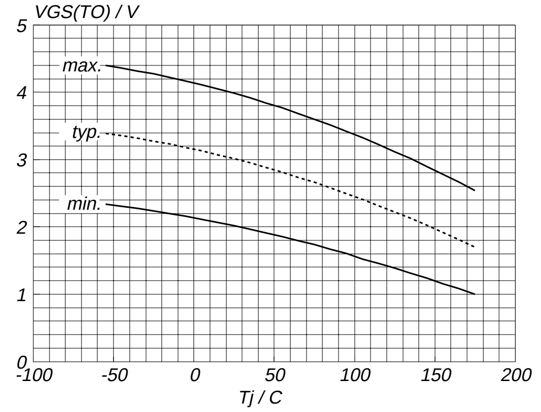


Fig.10. Gate threshold voltage.
$V_{GS(TO)} = f(T_j)$; conditions: $I_D = 1$ mA; $V_{DS} = V_{GS}$

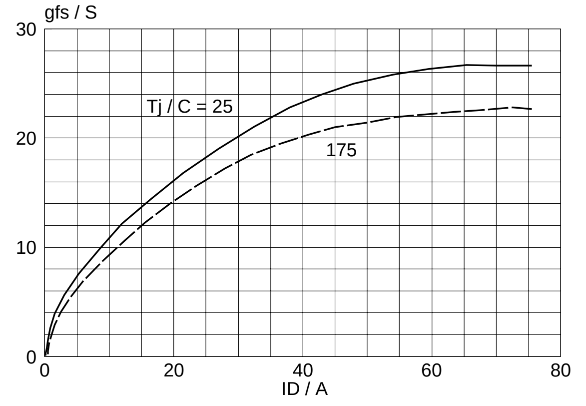


Fig.8. Typical transconductance, $T_j = 25$ ˚C.
$g_{fs} = f(I_D)$; conditions: $V_{DS} = 25$ V

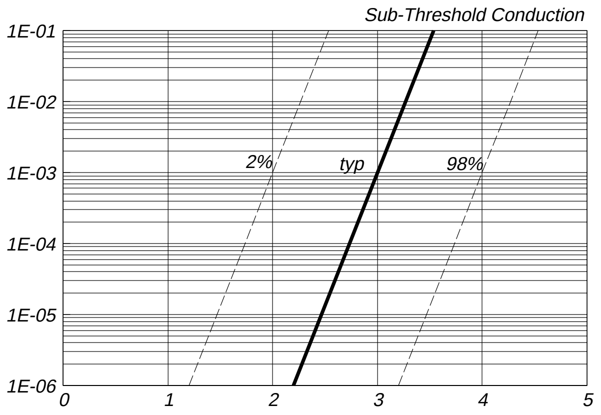


Fig.11. Sub-threshold drain current.
$I_D = f(V_{GS})$; conditions: $T_j = 25$ ˚C; $V_{DS} = V_{GS}$

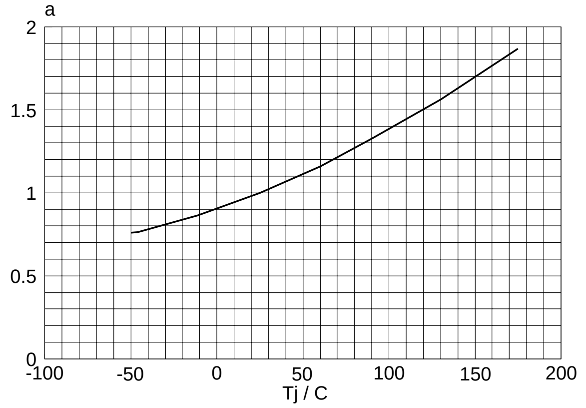


Fig.9. Normalised drain-source on-state resistance.
$a = R_{DS(ON)}/R_{DS(ON)25\,^{\circ}C} = f(T_j)$; $I_D = 25$ A; $V_{GS} = 10$ V

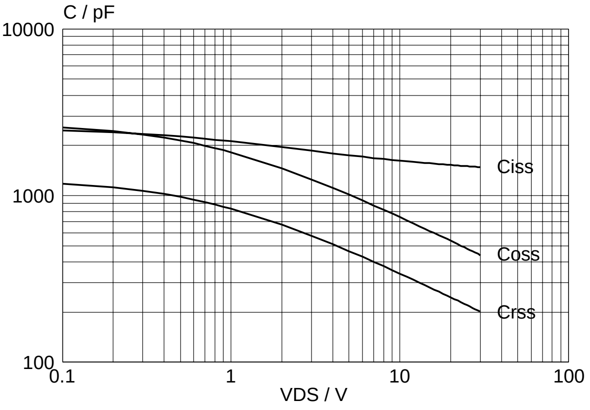


Fig.12. Typical capacitances, C_{iss}, C_{oss}, C_{rss}.
$C = f(V_{DS})$; conditions: $V_{GS} = 0$ V; f = 1 MHz

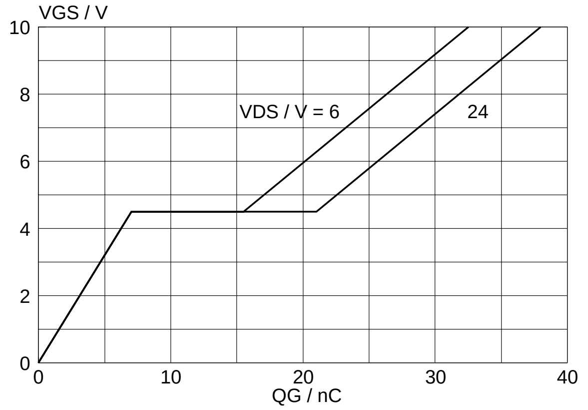


Fig.13. Typical turn-on gate-charge characteristics.
$V_{GS} = f(Q_G)$; conditions: I_D = 69 A; parameter V_{DS}

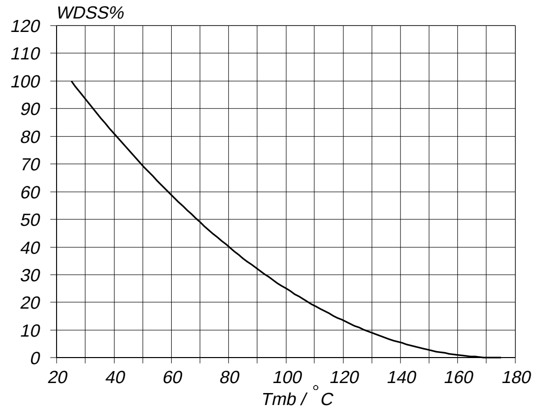


Fig.15. Normalised avalanche energy rating.
W_{DSS}% = $f(T_{mb})$; conditions: I_D = 35 A

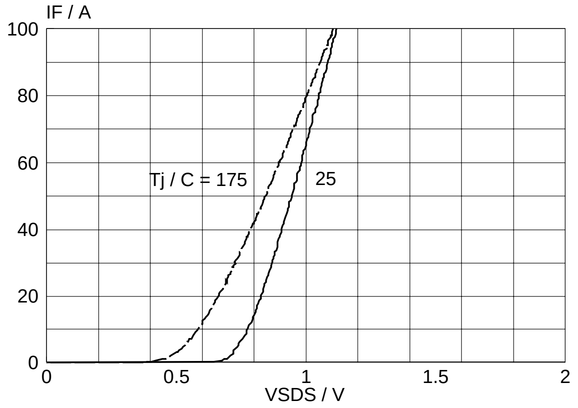


Fig.14. Typical reverse diode current.
$I_F = f(V_{SDS})$; conditions: V_{GS} = 0 V; parameter T_j

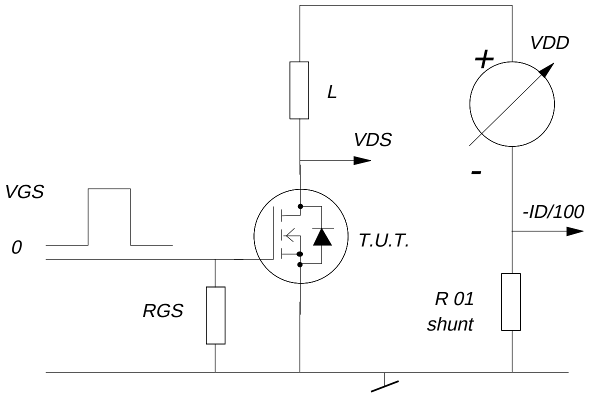


Fig.16. Avalanche energy test circuit.

$$W_{DSS} = 0.5 \cdot L I_D^2 \cdot BV_{DSS}/(BV_{DSS} - V_{DD})$$

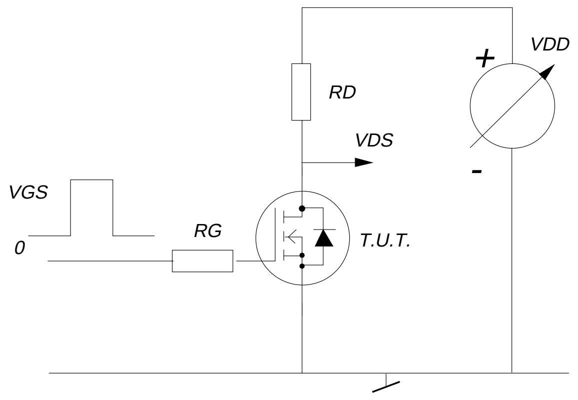


Fig.17. Switching test circuit.

MECHANICAL DATA

Dimensions in mm

Net Mass: 1.4 g

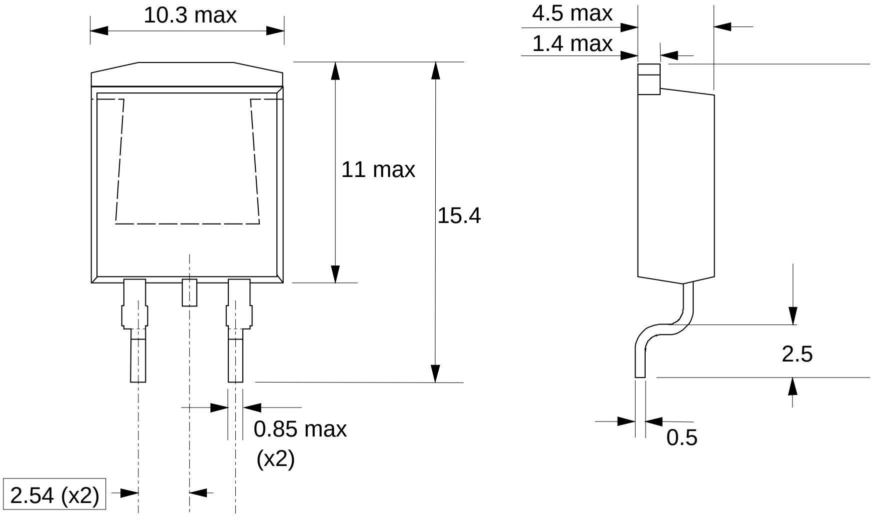


Fig.18. SOT404 : centre pin connected to mounting base.

MOUNTING INSTRUCTIONS

Dimensions in mm

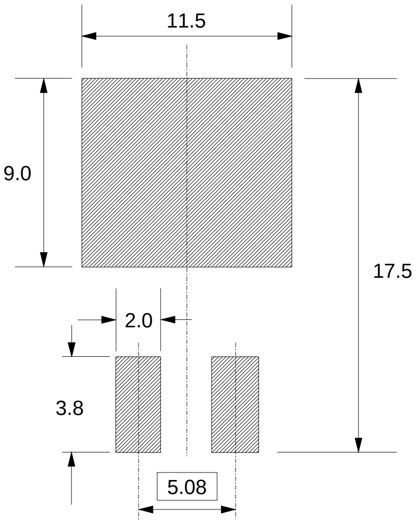


Fig.19. SOT404 : soldering pattern for surface mounting.

Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Epoxy meets UL94 V0 at 1/8".

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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